

Amendment to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (currently amended): A nickel alloy sputtering target for forming a film for preventing ~~Sn~~ tin (Sn) diffusion, ~~comprising:~~ said sputtering target consisting of 1 to 30at% of ~~Cu~~ copper (Cu); 2 to 25at% of at least one element selected from among ~~V, Cr, Al, Si, and Mo~~ vanadium (V), chromium (Cr), aluminum (Al), silicon (Si), and molybdenum (Mo); remnant ~~Ni~~ nickel (Ni) and unavoidable impurities.

Claim 2 (currently amended): The nickel alloy sputtering target according to claim 1, wherein the copper in said sputtering target exists in a solid solution, and wherein the nickel alloy is formed by adding said at least one element selected from among V, Cr, Al, Si, and Mo to a Ni-Cu solid solution.

Claim 3 (canceled).

Claim 4 (currently amended): A nickel alloy thin film formed between a solder bump and a substrate layer or a pad, ~~and~~ said nickel alloy thin film comprising 1 to 30at% of ~~Cu~~ copper (Cu); 2 to 25at% of at least one element selected from among ~~V, Cr, Al, Si, Ti and Mo~~ vanadium (V), chromium (Cr), aluminum (Al), silicon (Si), titanium (Ti) and molybdenum (Mo); remnant ~~Ni~~ nickel (Ni) and unavoidable impurities.

Claim 5 (currently amended): The nickel alloy thin film formed between a solder bump and a substrate layer or a pad according to claim 4, wherein the copper exists in a solid solution in said thin film, and wherein the nickel alloy is formed by adding said at least one element selected from among V, Cr, Al, Si, Ti and Mo to a Ni-Cu solid solution.

Claims 6-8 (canceled).

Claim 9 (previously presented): A nickel alloy thin film according to claim 5, wherein the solder bump is a Pb-free Sn solder or a Sn solder.

Claim 10 (previously presented): A nickel alloy thin film according to claim 9, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 11 (previously presented): A nickel alloy thin film according to claim 10, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 12 (previously presented): A nickel alloy thin film according to claim 4, wherein the solder bump is a Pb-free Sn solder or a Sn solder.

Claim 13 (previously presented): A nickel alloy thin film according to claim 12, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 14 (previously presented): A nickel alloy thin film according to claim 13, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 15 (previously presented): A nickel alloy thin film according to claim 4, further comprising a Cu-Sn intermetallic compound layer between the solder bump and the substrate layer or pad.

Claim 16 (previously presented): A nickel alloy thin film according to claim 15, wherein said Cu-Sn intermetallic compound layer is of a thickness of 0.01 to 5 μ m.

Claim 17 (currently amended): The nickel alloy sputtering target according to claim 2, further comprising ~~Ti~~ titanium (Ti), wherein a total amount of Ti together with said at least one element selected from among V, Cr, Al, Si and Mo is 2 to 25at%.

Claim 18 (currently amended): The nickel alloy sputtering target according to claim 1, further comprising ~~Ti~~ titanium (Ti), wherein a total amount of Ti together with said at least one element selected from among V, Cr, Al, Si and Mo is 2 to 25at%.

Claim 19 (new): A nickel alloy sputtering target, consisting of:

1 to 30at% of copper (Cu);

2 to 25at% of at least one element selected from among vanadium (V), chromium

(Cr), aluminum (Al), silicon (Si), and molybdenum (Mo); and

remnant nickel (Ni);

the copper in said sputtering target existing in a solid solution;

said sputtering target having a single phase metallographic structure and an

average grain size of 100 μ m or less; and

each of the copper, the at least one element, and the nickel of said sputtering

target being of a purity of at least 99.9% (3N).

Claim 20 (new): A nickel alloy sputtering target according to claim 19, wherein said purity is at least 99.999% (5N).